

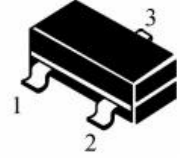


# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

BAS16/BAW56/BAV70/BAV99

## SOT-23 Switching Diode 开关二极管



### Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	BAS16	BAW56	BAV70	BAV99
Pin 管脚				
Mark 打标	A6	A1	A4	A7

### Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	$V_{RRM}$	70	V
Reverse Work Voltage 反向工作电压	$V_{RWM}$		
DC Reverse Voltage 直流反向电压	$V_R$		
Forward Work Current 正向工作电流	$I_F(I_O)$	200	mA
Peak Forward Current 正向峰值电流	$I_{FM}$	300	mA
Power dissipation 耗散功率	$P_D(T_a=25^\circ C)$	225	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	555	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+150 $^\circ C$	

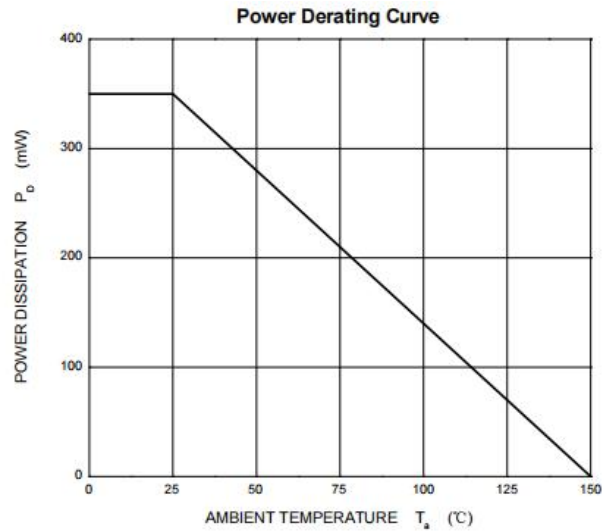
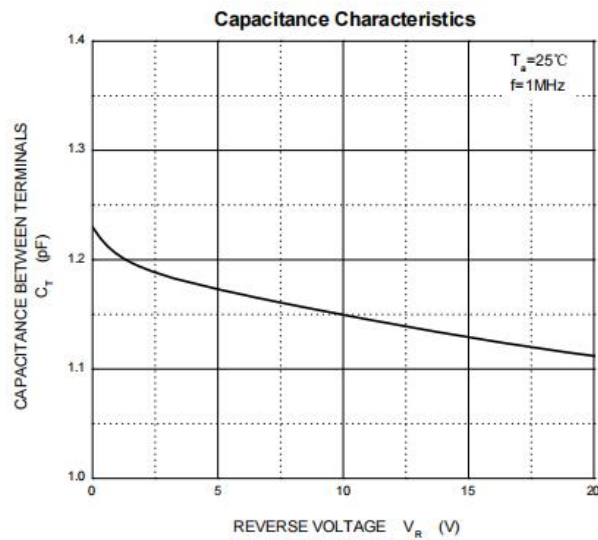
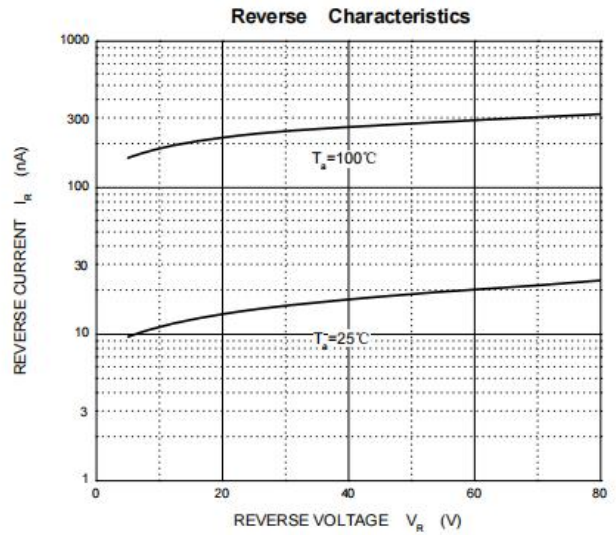
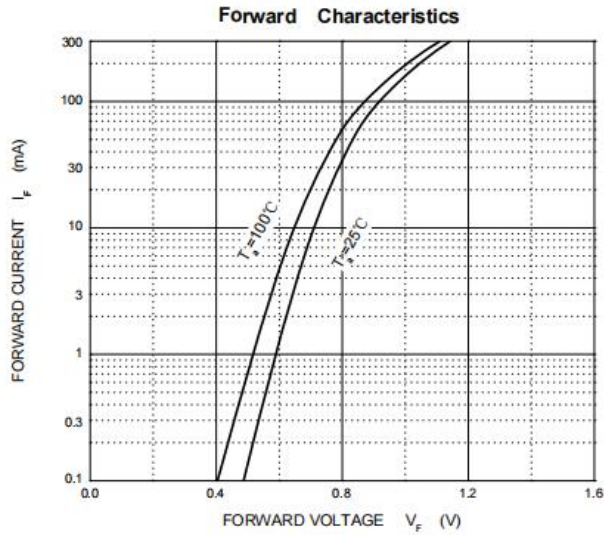
### Electrical Characteristics 电特性

( $T_A=25^\circ C$  unless otherwise noted 如无特殊说明, 温度为  $25^\circ C$ )

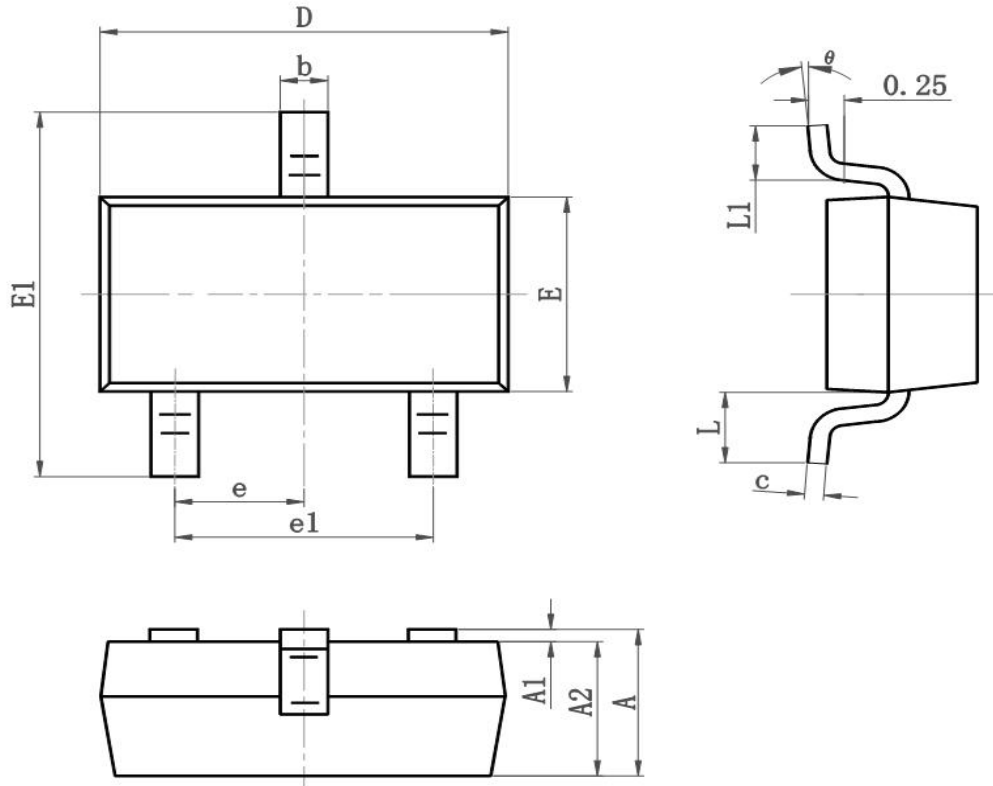
Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压( $I_R=100\mu A$ )	$V_{(BR)}$	70	—	V
Reverse Leakage Current 反向漏电流( $V_R=70V$ )	$I_R$	—	2.5	$\mu A$
Forward Voltage( $I_F=1mA$ ) 正向电压( $I_F=10mA$ ) ( $I_F=50mA$ ) ( $I_F=150mA$ )	$V_F$	—	0.715 0.855 1.0 1.25	V
Diode Capacitance 二极管电容( $V_R=0V, f=1MHz$ )	$C_D$	—	1.5	pF
Reverse Recovery Time 反向恢复时间	$T_{rr}$	—	6	nS



## ■ Typical Characteristic Curve 典型特性曲线



## Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°